

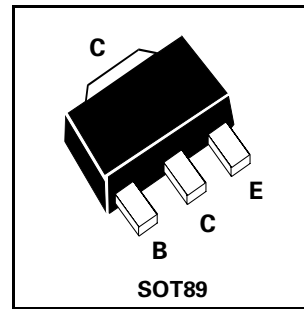
SOT89 NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

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BSR43

COMPLEMENTARY TYPES – BSR33

PARTMARKING DETAIL – AR4



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	90	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	2	A
Continuous Collector Current	I_C	1	A
Base Current	I_B	100	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{TOT}	1	W
Operating and Storage Temperature Range	$T_j:T_{stg}$	-65 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	90		V	$I_C=100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80		V	$I_C=10mA$ *
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		V	$I_E=10\mu A$
Collector Cut-Off Current	I_{CBO}		100 50	nA μA	$V_{CB}=60V$ $V_{CB}=60V, T_{amb} = 125^{\circ}C$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25 0.5	V V	$I_C = 150mA, I_B = 15mA$ $I_C = 500mA, I_B = 50mA$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.0 1.2	V V	$I_C = 150mA, I_B = 15mA$ $I_C = 500mA, I_B = 50mA$
Static Forward Current Transfer Ratio	h_{FE}	30 100 50	300		$I_C = 100\mu A, V_{CE} = 5V$ $I_C = 100mA, V_{CE} = 5V$ $I_C = 500mA, V_{CE} = 5V$
Output Capacitance	C_{obo}		12	pF	$V_{CB} = 10V, f=1MHz$
Input Capacitance	C_{ibo}		90	pF	$V_{EB} = 0.5V, f=1MHz$
Transition Frequency	f_T	100		MHz	$I_C=50mA, V_{CE}=10V$ $f = 35MHz$
Turn-On Time	T_{on}		250	ns	$V_{CC}=20V, I_C = 100mA$
Turn-Off Time	T_{off}		1000	ns	$I_{B1} = I_{B2} = 5mA$

*Measured under pulsed conditions.

For typical characteristics graphs see FMMT493 datasheet.

